

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Supply Voltage	Vcc	50	V
Input Voltage	V _{IN}	-10 to +40	V
Output Current	lo	50	mA
Collector Current	I _{C(MAX)}	100	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	250	mW
Power Derating above +25°C	P _{der}	2	mW/°C
Thermal Resistance, Junction to Ambient Air (Note 5) (Equivalent to one heated junction of NPN)	$R_{ hetaJA}$	500	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Off Characteristics (Note 6)					•	
Collector-Base Breakdown Voltage	BV _{CBO}	50	_	_	V	$I_C = 50\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	50	_	_	V	$I_C = 1.0 \text{mA}, I_B = 0$
Collector Cutoff Current	I _{CEX}	_	_	0.5	μΑ	$V_{CE} = 50V, V_{EB(OFF)} = 3.0V$
Collector-Base Cut Off Current	I _{CBO}	_	_	0.1	μΑ	$V_{CB} = 50V, I_{E} = 0$
Collector-Emitter Cut Off Current, IO(OFF)	I _{CES}	_	_	0.1	μΑ	$V_{CB} = 50V, I_B = 0$
Emitter-Base Cut Off Current	I _{EBO}	_	_	800	μΑ	$V_{EB} = 10V, I_{C} = 0$
Input Off Voltage	V _{I(off)}	0.5	1.16	_	V	$V_{CC} = 5V, I_{O} = 100\mu A$
Input On Voltage	V _{I(on)}			2.5	V	$V_{CC} = 0.3V, I_{O} = 10mA$
On Characteristics (Notes 6 & 7)						
		10	_	_		$V_{CE} = 5V$, $I_C = 1mA$
		15	_	_	_	$V_{CE} = 5V$, $I_C = 2mA$
DC Current Gain	h _{FE}	60	_	_		$V_{CE} = 5V$, $I_C = 10mA$
		100	_	_	_	$V_{CE} = 5V$, $I_C = 50mA$
		90	_	_		$V_{CE} = 5V$, $I_C = 70mA$
	VCE(sat)	_	_	0.15	V	$I_C = 10mA$, $I_B = 1mA$
		_	_	0.2	V	$I_C = 50$ mA, $I_B = 5$ mA
Collector-Emitter Saturation Voltage		_	_			
		_	_	0.25	V	$I_C = 50 \text{mA}, I_B = 10 \text{mA}$
		_	_	0.3	V	I _C = 70mA, I _B = 10mA
Dago Emittor Turn On Voltage	V _{BE(on)}	_	_	0.85	V	$V_{CE} = 5V$, $I_C = 2mA$
Base-Emitter Turn-On Voltage		_	_	0.95	V	$V_{CE} = 5V$, $I_C = 10mA$
Dage Emitter Coturation Voltage	V _{BE(sat)}	_	_	0.98	V	I _C = 10mA, I _B = 1mA
Base-Emitter Saturation Voltage		_	_	1.2	V	$I_C = 50$ mA, $I_B = 5$ mA
Input Current	l _l	_	_	0.88	mA	$V_I = 5V$
Output On Voltage (Same as V _{CE(sat)})	V _{O(on)}	_	_	0.25	V	$I_1 = 2.5 \text{mA}, I_0 = 50 \text{mA}$
Input Resistance	R1	7	10	13	kΩ	_
Resistance Ratio	(R2/R1)	0.8	1	1.2		
Small Signal Characteristics	Small Signal Characteristics					
Current Gain-Bandwidth Product	f _T	_	250	_	MHz	V _{CE} = 10V, I _E = 5mA, f = 1MHz

- 5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air 5. For the evice modified of minimum recommended pad layout 102 copper that is of a single-sided 1.5mm r (4 p conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
 6. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.
 7. Guaranteed by design.



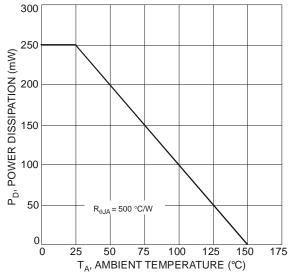


Fig. 1 Power Dissipation vs. Ambient Temperature

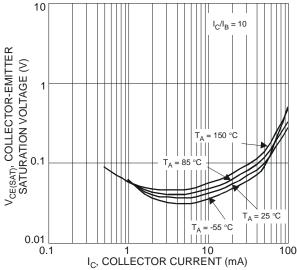


Fig. 3 Typical Collector Emitter Saturation Voltage vs. Collector Current

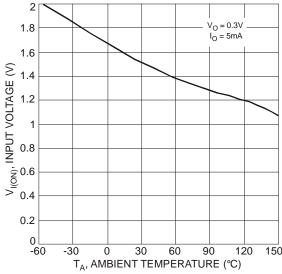


Fig. 5 Typical Input Voltage vs. Ambient Temperature

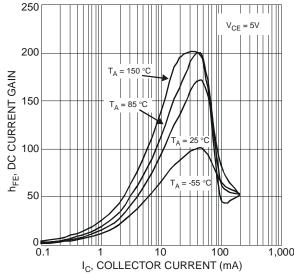


Fig. 2 Typical DC Current Gain vs. Collector Current

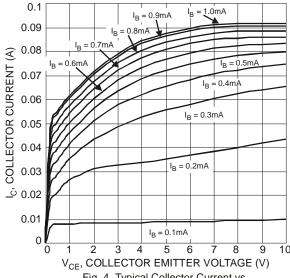


Fig. 4 Typical Collector Current vs.
Collector Emitter Voltage

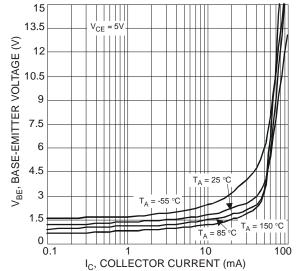
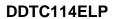


Fig. 6 Typical Base-Emitter Voltage vs. Collector Current





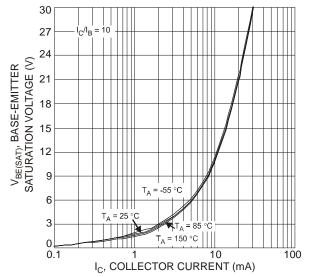
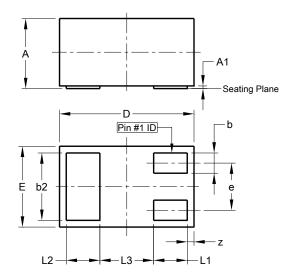


Fig. 7 Typical Base Emitter Saturation Voltage vs. Collector Current



Package Outline Dimensions

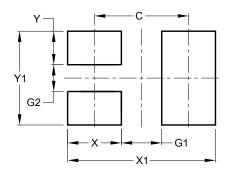
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X1-DFN1006-3				
Dim	Min	Max	Тур	
Α	0.47	0.53	0.50	
A1	0.00	0.05	0.03	
b	0.10	0.20	0.15	
b2	0.45	0.55	0.50	
D	0.95	1.075	1.00	
E	0.55	0.675	0.60	
е	-	-	0.35	
L1	0.20	0.30	0.25	
L2	0.20	0.30	0.25	
L3	-	-	0.40	
Z	0.02	0.08	0.05	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Υ	0.25
Y1	0.70



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